

N-channel TrenchMOS intermediate level FET Rev. 01 — 4 October 2010

Product data sheet

1. **Product profile**

1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Suitable for standard and logic level gate drive sources

1.3 Applications

- 12 V and 24 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control

1.4 Quick reference data

Table 1. **Quick reference data**

- Suitable for thermally demanding environments due to 175 °C rating
- Start-Stop micro-hybrid applications

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- Transmission control
- Ultra high performance power switching

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	55	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u>	-	-	31	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see Figure 2	-	-	60	W
Static char	racteristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; see <u>Figure 11</u>	-	24.8	29	mΩ
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 31 \; A; \; V_{sup} \leq 55 \; V; \\ R_{GS} &= 50 \; \Omega; \; V_{GS} = 10 \; V; \\ T_{j(\text{init})} &= 25 \; ^\circ\text{C}; \; \text{unclamped} \end{split} $	-	-	25	mJ
Dynamic o	haracteristics					
Q _{GD}	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 44 \text{ V};$ $V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure } 13}{\text{see } \frac{\text{Figure } 14}{\text{Figure } 14}}$	-	5.76	-	nC

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2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT428 (DPAK)	

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BUK6228-55C	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
-						
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	55	V
V _{GS}	gate-source voltage	DC	<u>[1]</u>	-16	16	V
		Pulsed	[2]	-20	20	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>		-	31	А
		T_{mb} = 100 °C; V_{GS} = 10 V; see <u>Figure 1</u>		-	22	А
I _{DM}	peak drain current	T _{mb} = 25 °C; t _p ≤ 10 μs; pulsed; see <u>Figure 3</u>		-	122	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	60	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	diode					
I _S	source current	T _{mb} = 25 °C		-	31	А
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	122	А
Avalanche rug	ggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 31 A; $V_{sup} \le 55$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	25	mJ
E _{DS(AL)R}	repetitive drain-source avalanche energy		<u>[3][4][5]</u>	-	-	J

[1] -16V accumulated duration not to exceed 168 hrs

[2] Accumulated pulse duration not to exceed 5 mins.

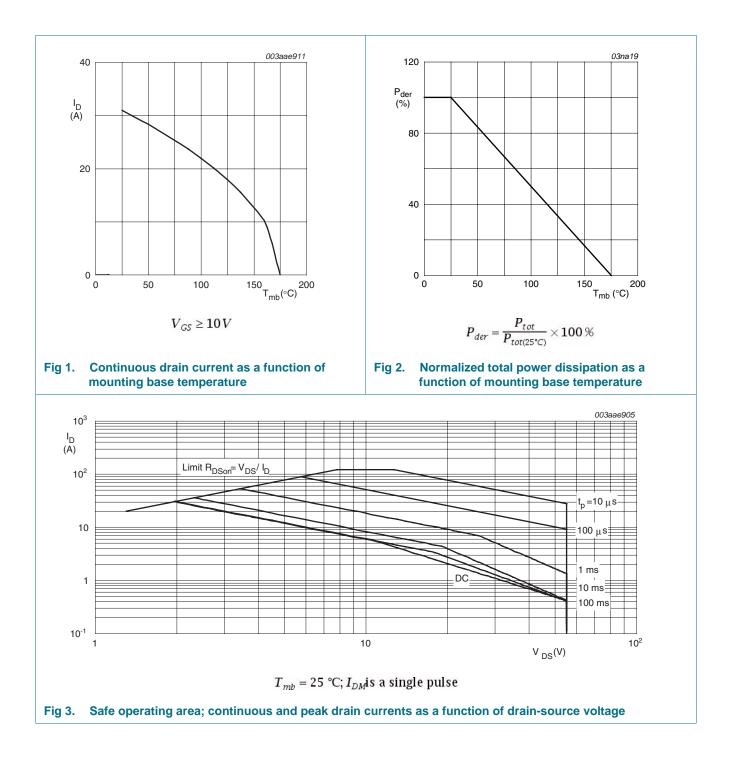
[3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[4] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

[5] Refer to application note AN10273 for further information.

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5. Thermal characteristics

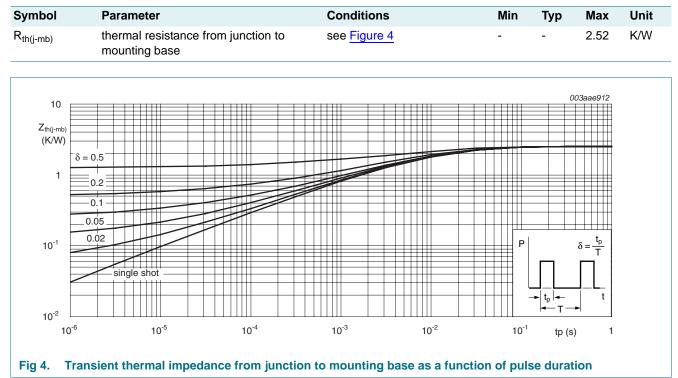


Table 5. Thermal characteristics

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6. Characteristics

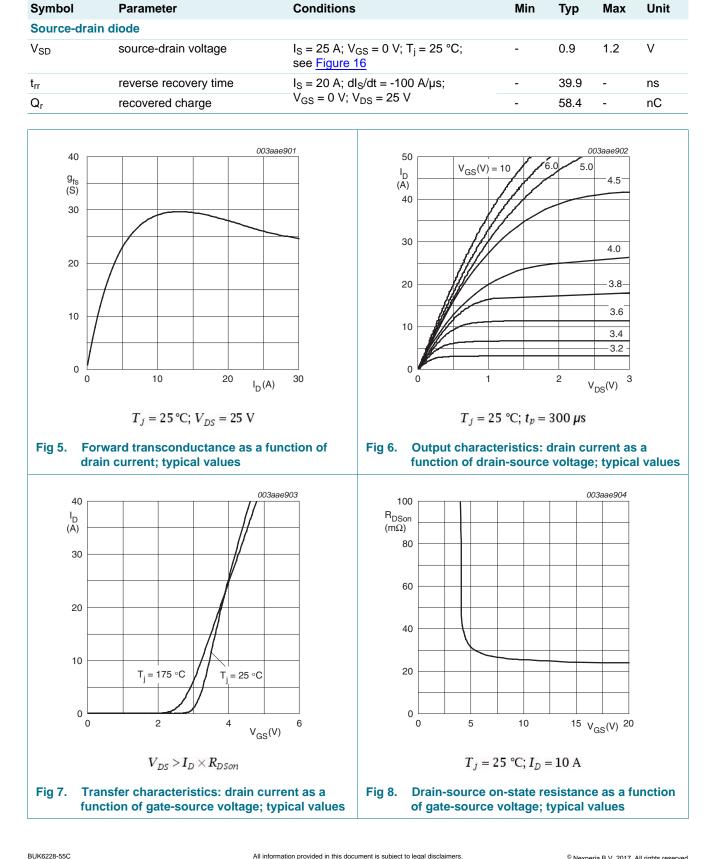
Table 6.	Characteristics			_		
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	racteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	55	-	-	V
	voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	50	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 9</u> ; see <u>Figure 10</u>	1.8	2.3	2.8	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 10</u>	-	-	3.3	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 10</u>	0.8	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	0.02	1	μΑ
I _{GSS}	gate leakage current	$V_{DS} = 0 V; V_{GS} = 20 V; T_j = 25 °C$	-	2	100	nA
		$V_{DS} = 0 V; V_{GS} = -20 V; T_j = 25 °C$	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; see <u>Figure 11</u>	-	24.8	29	mΩ
		V_{GS} = 5 V; I_D = 10 A; T_j = 25 °C; see <u>Figure 11</u>	-	30.3	38	mΩ
		V _{GS} = 4.5 V; I _D = 10 A; T _j = 25 °C; see <u>Figure 11</u>	-	32.9	44	mΩ
		V_{GS} = 10 V; I_D = 10 A; T_j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 11</u>	-	-	64	mΩ
Dynamic o	haracteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 5 \text{ V};$ see <u>Figure 13</u> ; see <u>Figure 14</u>	-	11	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$	-	20.2	-	nC
Q _{GS}	gate-source charge	see Figure 13; see Figure 14	-	3.73	-	nC
Q _{GD}	gate-drain charge		-	5.76	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;	-	1003	1340	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } Figure 15$	-	102	123	pF
C _{rss}	reverse transfer capacitance		-	70	96	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 45 \text{ V}; \text{ R}_{L} = 1.8 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	6.6	-	ns
t _r	rise time	$R_{G(ext)} = 10 \ \Omega$	-	21.9	-	ns
t _{d(off)}	turn-off delay time		-	22.5	-	ns
t _f	fall time		-	10.6	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to centre of die ; $T_j = 25 ^\circ\text{C}$	-	3.5	-	nH
L _S	internal source inductance	from source lead to source bond pad ; $T_j = 25 \text{ °C}$	-	7.5	-	nH

Table 6.

Characteristics ... continued

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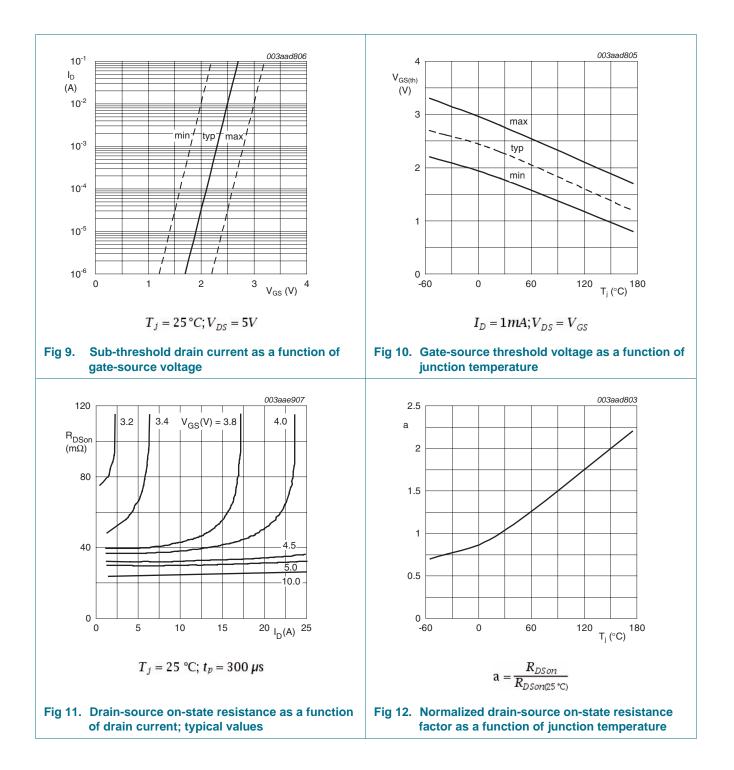
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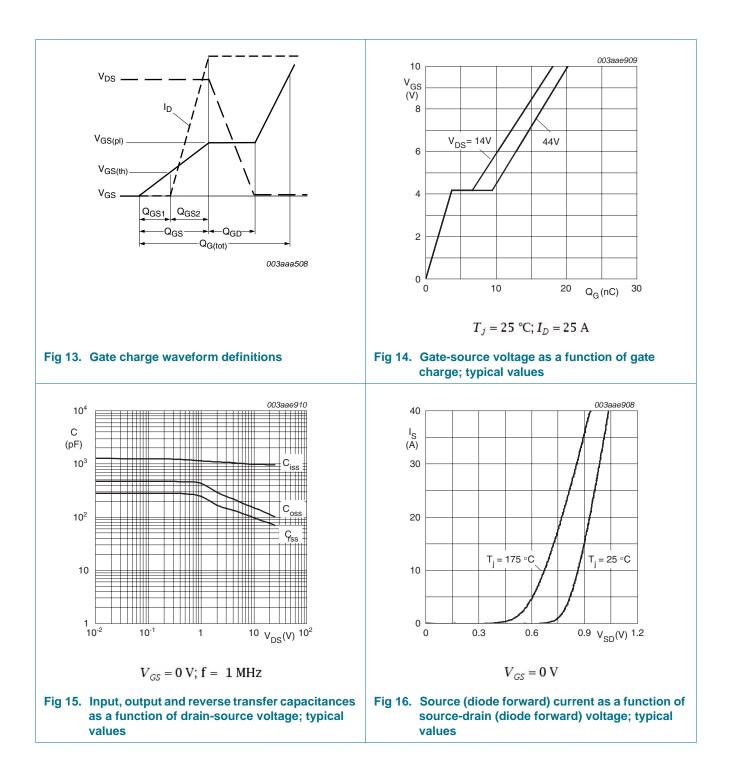
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Package outline 7.

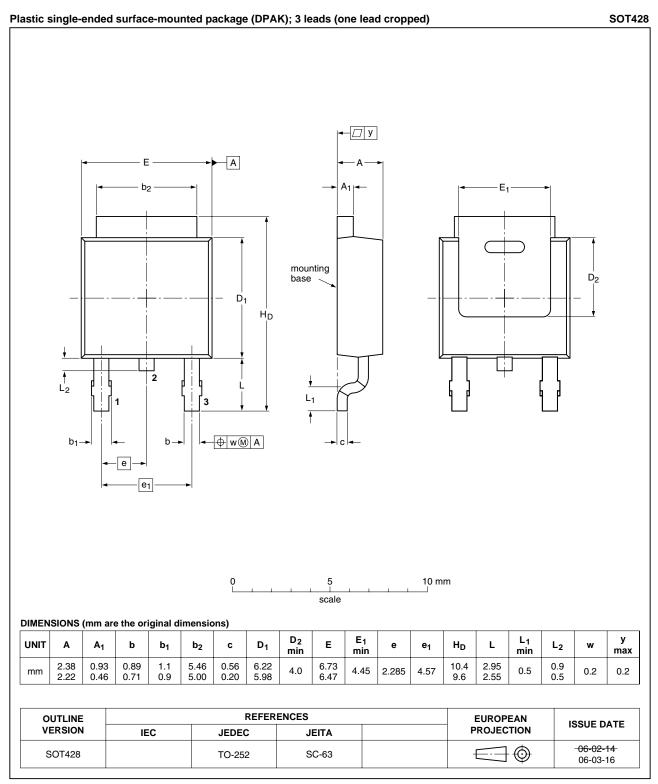


Fig 17. Package outline SOT428 (DPAK)

BUK6228-55C

Product data sheet

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8. Revision history

Table 7. Revision history					
Document ID	Release date	Data sheet status	Change notice	Supersedes	
BUK6228-55C v.1	20101004	Product data sheet	-	-	

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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